

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (original): A semiconductor package comprising:
  - a low-K Si die having front and back surfaces, the low-K Si die including a plurality of layers of low-K material;
  - a packaging substrate having die and board surfaces;
  - a heat spreader;
  - a thermal interface material coupling the heat spreader to the back surface of the low-K Si die, the thermal interface material having a thermal interface material modulus that is higher than or equal to 100 MPa; and
  - an adhesive coupling the heat spreader to the die surface of the packaging substrate, the adhesive having an adhesive modulus that is lower than or equal to 10 MPa.
2. (original): A semiconductor package as recited in claim 1, wherein the low-K Si die is stably integrated within the semiconductor package such that the reliability of the low-K Si die is not substantially impaired by internal stress of the semiconductor package, the internal stress being created from cycling the temperature of the semiconductor package from -55 °C to 125 °C.
3. (original): A semiconductor package as recited in claim 1, wherein the low-K Si die is an extra low-K Si die including a plurality of layers of extra low-K material.
4. (original): A semiconductor package as recited in claim 1, wherein the layer of low-K material has a thickness of 6 microns or less.
5. (original): A semiconductor package as recited in claim 1, wherein the low-K Si die has a thickness in the range of 19 mil to 28 mil.
6. (original): A semiconductor package as recited in claim 1, wherein the low-K Si die size ranges from 2 mm x 2 mm to 30 mm x 30 mm.

7. (original): A semiconductor package as recited in claim 1, wherein the packaging substrate size ranges up to 45 mm x 45 mm.

8. (original): A semiconductor package as recited in claim 1, wherein the thermal interface material is has a modulus about 400 MPa.

9. (original): A semiconductor package as recited in claim 1, wherein the adhesive has a modulus about 4 MPa.

10. (original): A semiconductor package as recited in claim 1, wherein the front surface of the low-K Si die is electrically and mechanically coupled with the die surface of the packaging substrate.

11. (original): A semiconductor package as recited in claim 10, wherein the low-K Si die includes a plurality of solder bumps on the front surface of the low-K Si die for electrically and mechanically coupling the front surface of the low-K Si die with the die surface of the packaging substrate.

12. (original): A semiconductor package as recited in claim 11, wherein the plurality of solder bumps offset the low-K Si die from the packaging substrate such that a gap is formed in between the front surface of the low-K Si die and the die surface of the packaging substrate.

13. (original): A semiconductor package as recited in claim 12, wherein the gap is filled with an underfill material.

14-25 (canceled)

26. (original): A semiconductor package, comprising:

a low-K Si die having front and back surfaces and a packaging substrate having die and board surfaces, the low-K Si die including a plurality of layers of low-K material;

means for electrically and mechanically coupling the front surface of the low-K Si die with the die surface of the packaging substrate;

means for connecting a heat spreader to the back surface of the low-K Si die with a thermal interface material having a modulus that is higher than or equal to 100 MPa; and

means for connecting the heat spreader to the die surface of the packaging substrate with an adhesive having a modulus that is lower than or equal to 10 MPa.